Features

- Spilt Gate Trench MOSFET Tecnology
- Excellent Package For Heat Dissipation
- High Density Cell Design For Low $R_{ds(on)}$
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

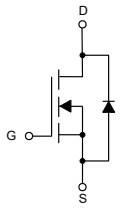
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 140°C/W Junction to Ambient(Note 2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	3	A
	T_A=70°C		2.4	
Pulsed Drain Current (Note 3)		I_{DM}	12	A
Total Power Dissipation(Note 4)		P_D	0.9	W

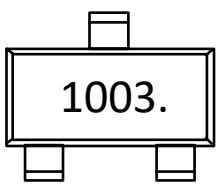
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. Pd is based on max. junction temperature, using junction-ambient thermal resistance.

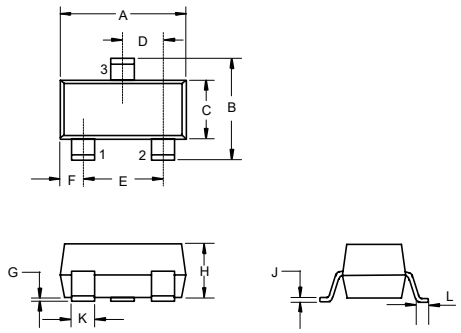
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

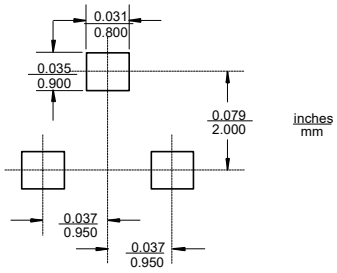


SOT-23



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	100			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=3A		110	140	mΩ
		V_{GS}=4.5V, I_D=2A		160	300	
Gate Resistance	R_g	f=1 MHz, Open drain		2.0		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				3	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=3A		0.8	1.2	V
Reverse Recovery Time	t_{rr}	I_S=3A,di/dt=100A/μs		30		ns
Reverse Recovery Charge	Q_{rr}			25		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V,f=1MHz		135		pF
Output Capacitance	C_{oss}			28		
Reverse Transfer Capacitance	C_{rss}			1.2		
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=10V,I_D=3A		3.2		nC
Gate-Source Charge	Q_{gs}			0.5		
Gate-Drain Charge	Q_{gd}			1.1		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=50V, I_D=3.0A, R_G=2Ω		3		ns
Turn-On Rise Time	t_r			18		
Turn-Off Delay Time	$t_{d(off)}$			10		
Turn-Off Fall Time	t_f			18.6		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

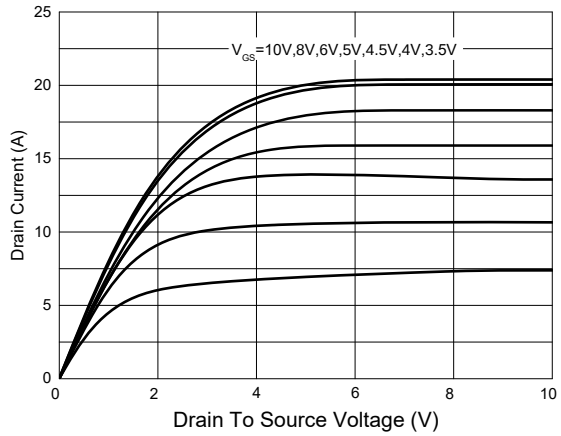


Fig.2 Transfer Characteristic

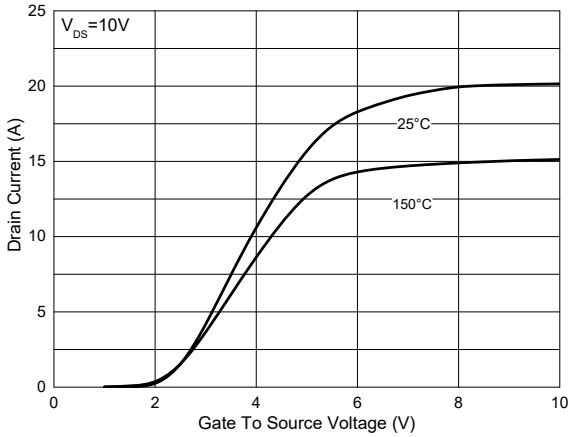


Fig.3 Rdson-Vgs

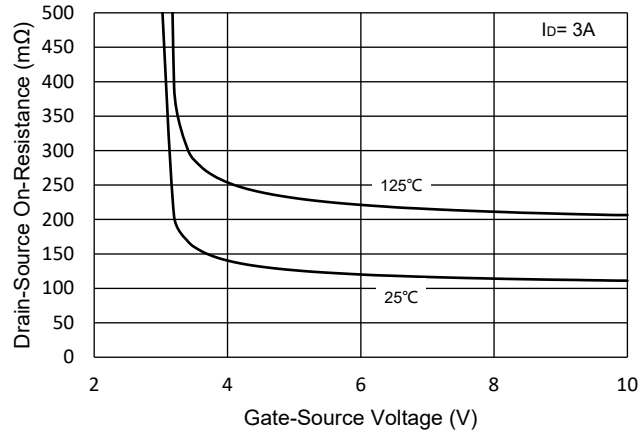


Fig.4 $R_{DS(ON)}$-I_D

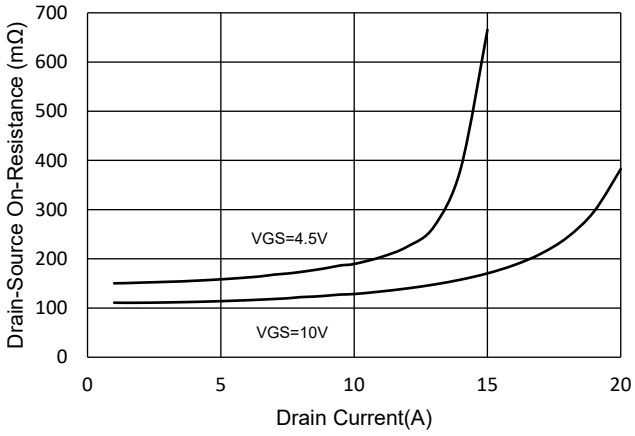


Fig.5 Capacitance Characteristics

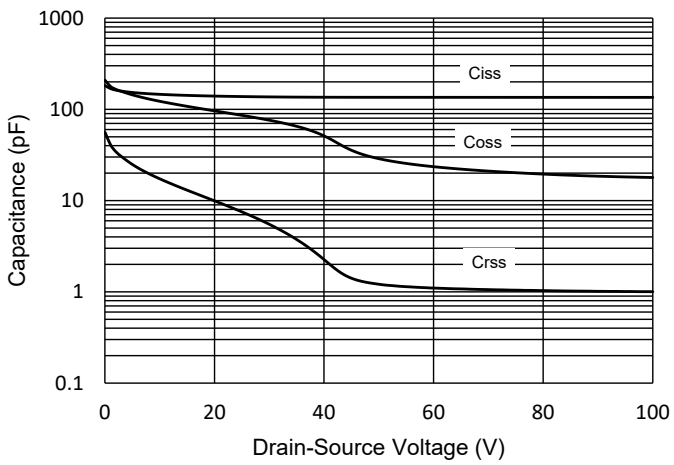
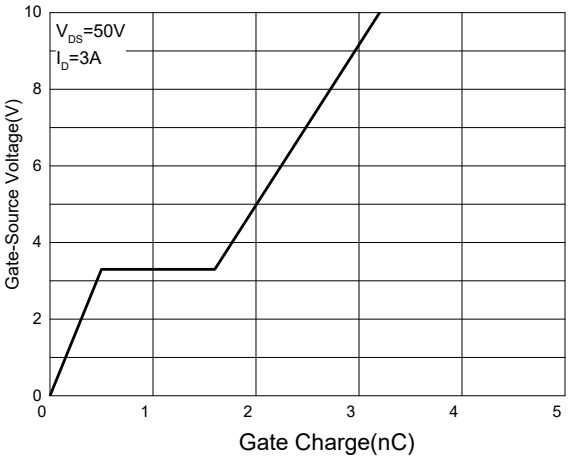


Fig. 6 - Gate Charge



Curve Characteristics

Fig.7 Normalized Threshold Voltage

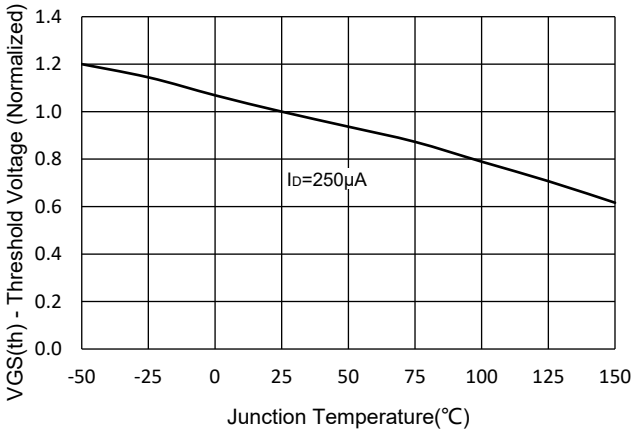


Fig.8 Normalized On Resistance Characteristics

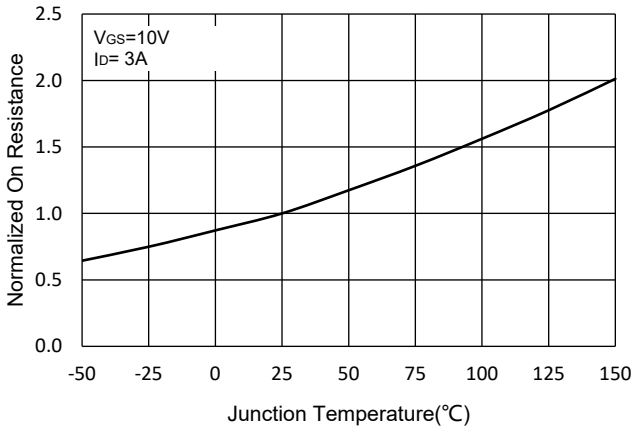


Fig.9 IS-VSD

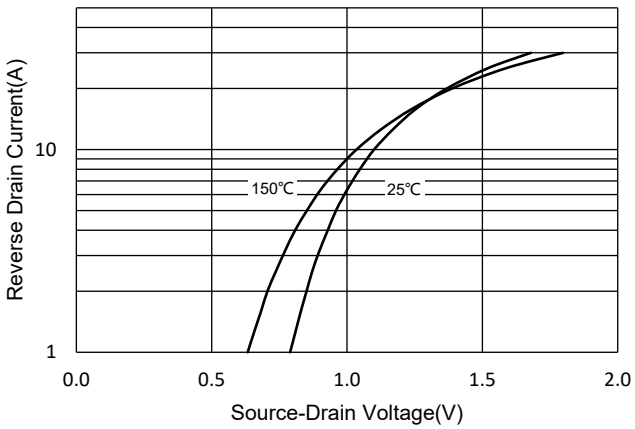


Fig.10 Drain Current

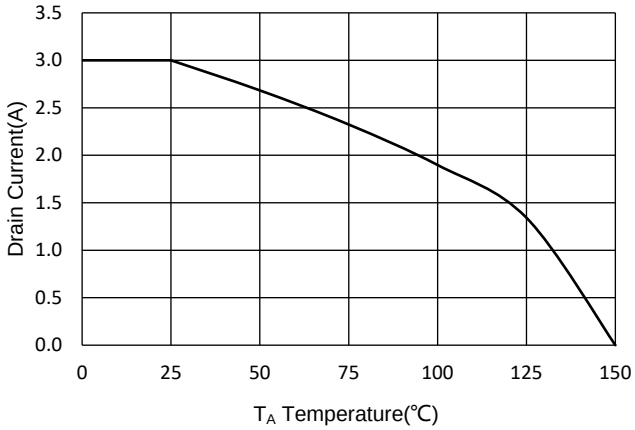
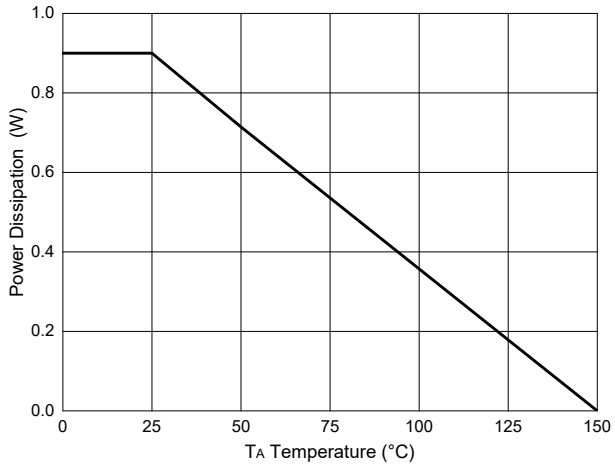


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

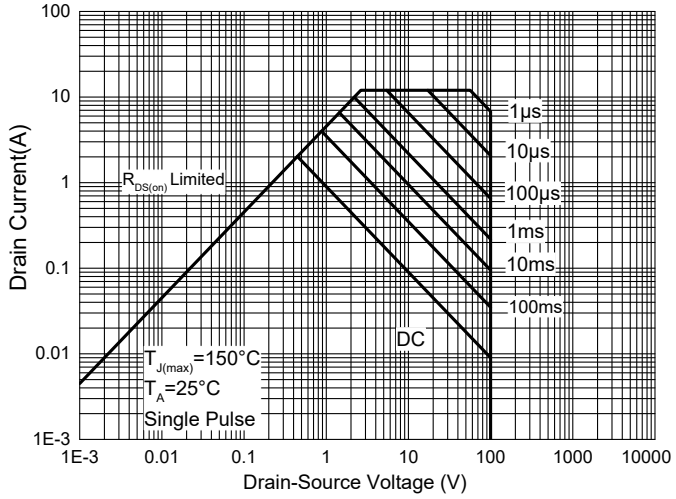
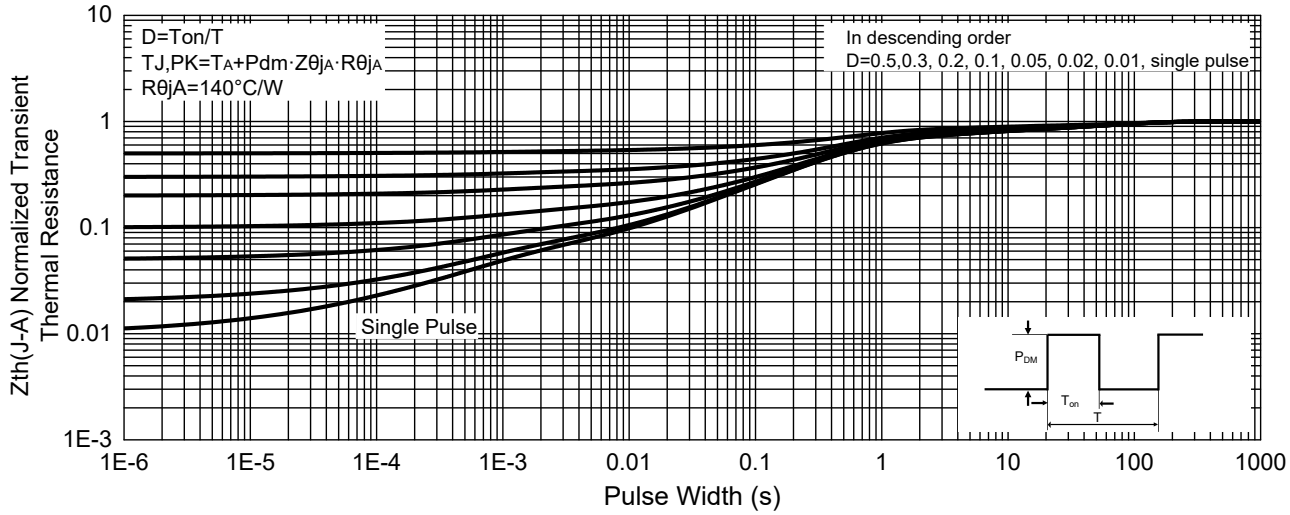


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel